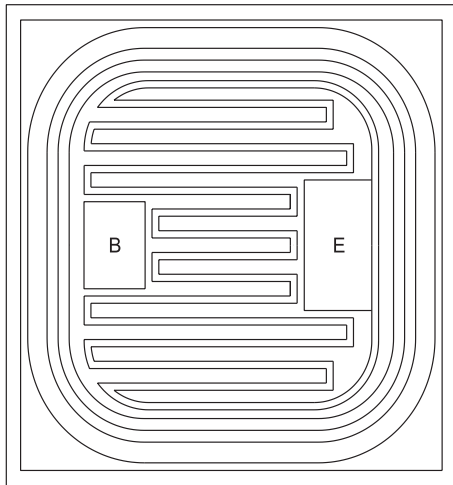


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	63 x 63 MILS
Die Thickness	10 MILS
Base Bonding Pad Area	9 x 12 MILS
Emitter Bonding Pad Area	10 x 18 MILS
Top Side Metalization	Al - 16,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 4 INCH WAFER

2,840

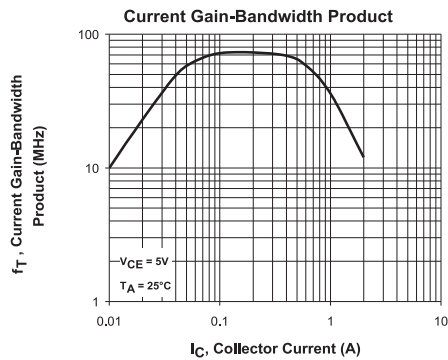
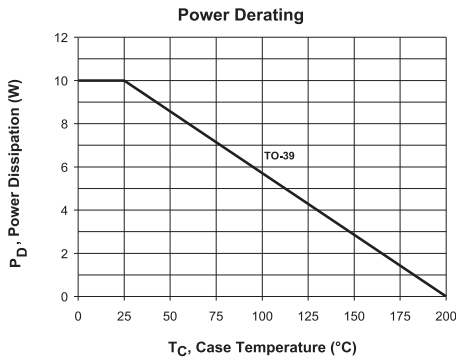
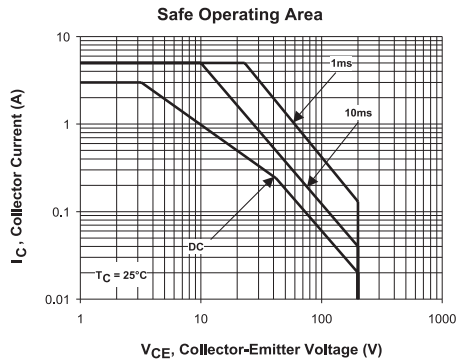
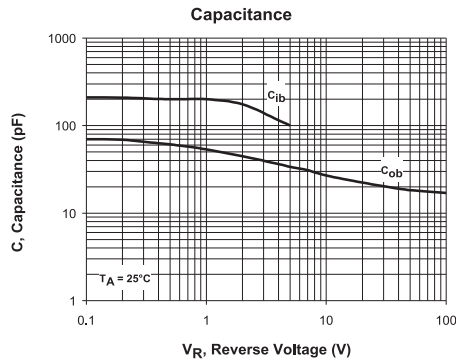
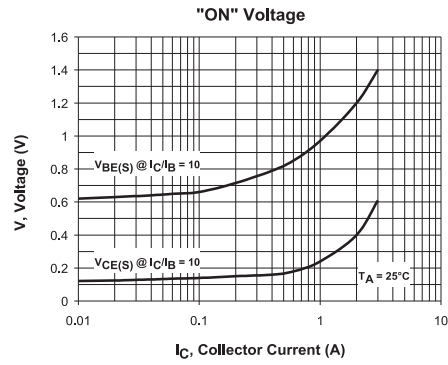
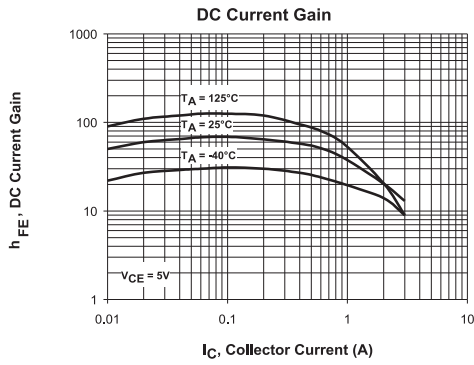
PRINCIPAL DEVICE TYPES

BUY49S

BSW68

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centalsemi.com

R1 (1-August 2002)



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